

ABSTRACT

5 The present invention provides a high resistivity,
high quality, large size SiC single crystal, SiC single
crystal wafer, and method of production of the same, that
is, a silicon carbide single crystal containing
uncompensated impurities in an atomic number density of $1 \times 10^{15}/\text{cm}^3$ or more and containing vanadium in an amount
less than said uncompensated impurity concentration,
10 silicon carbide single crystal wafer obtained by
processing and polishing the silicon carbide single
crystal and having an electrical resistivity at room
temperature of $5 \times 10^3 \Omega\text{cm}$ or more, and a method of
production of a silicon carbide single crystal.